

Feature :

Frequency: 5.9~6.4GHz

Output Power: $P_{out} \geq 45\text{dBm}$

Gain : $\geq 8\text{dB}$

PAE : $\geq 35\%$

Port matching : $Z_{in}/Z_{out} = 50\Omega$

Description :

XYC059064-P45 is a GaAs internal matching power tube. It adopts advanced in-plane matching synthesis technology and mature film hybrid integration process. The typical operating frequency band of the product is 5.9~6.4GHz, with high power, high efficiency and temperature. It can be widely used in various RF/microwave systems due to its environmental adaptability.

Max Rating (TC=25°C) :

	Symbol	Value	Unit
VDS	V_{DS}	12	V
VGS	V_{GS}	-5	V
Storage Temperature	T_{stg}	-65 to +175	°C
Channel Temperature	T_{ch}	175	°C

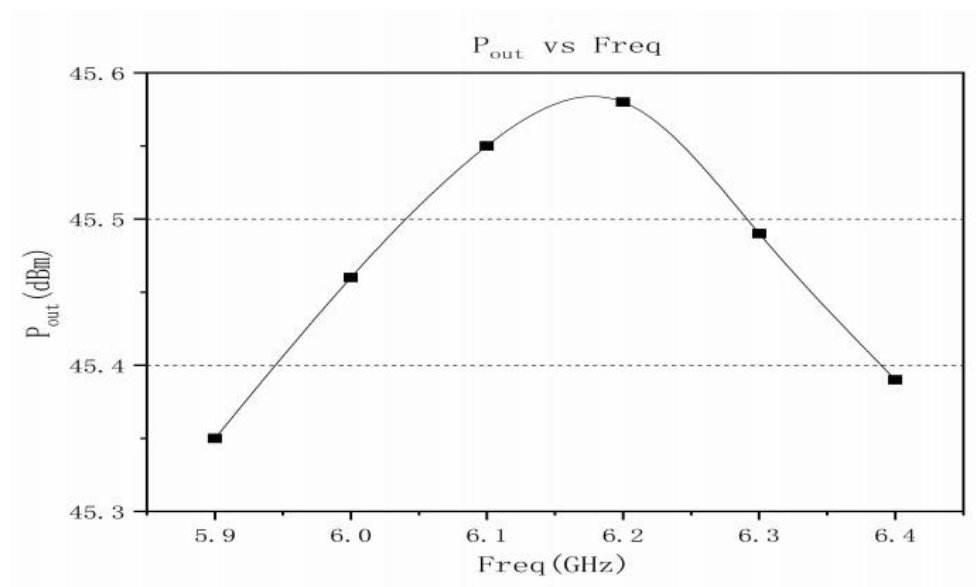
Quanzhou Yingtron Microwave Electronics Co., Ltd.

Add: 23F, Agriculture Bank Building, Quanzhou, Fujian, China
TEL: 0595-28071010 FAX: 0595-22188000
www.yingtron.com

Electrical Performance :

	symbol	Test Conditions	Value			Unit
			Min	Typ	Max	
Drain current	I_{dsr}	$V_{DS}=28V$	-	7	-	A
Output Power	P_{out}	CW Operation	45	45.5	-	dBm
Power gain	G_p	$P_{in} : 37dBm$	8	8.5	-	dB
Work efficiency	PAE	Freq : 5.9~6.4GHz	35	-	-	%
Gain flatness	ΔG		-0.8	-	+0.8	dB

Typical Curve :



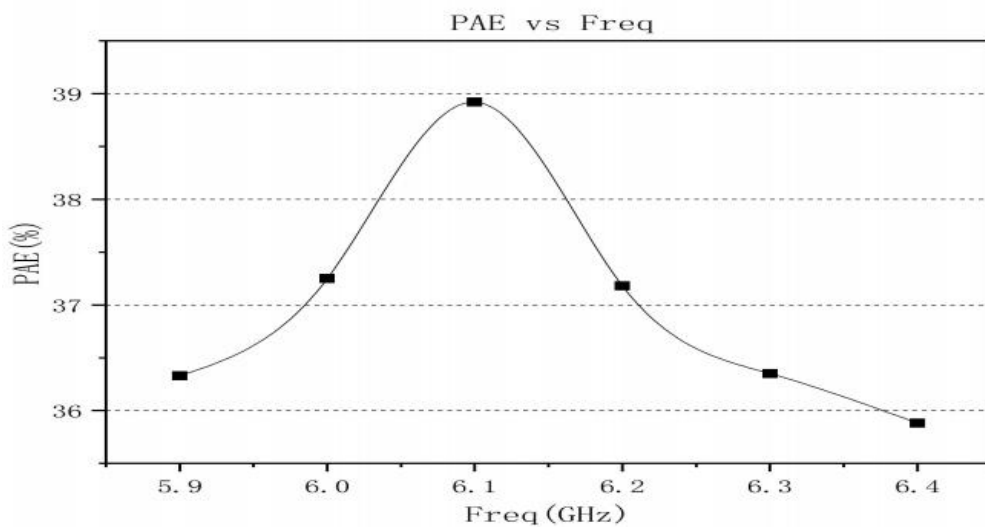
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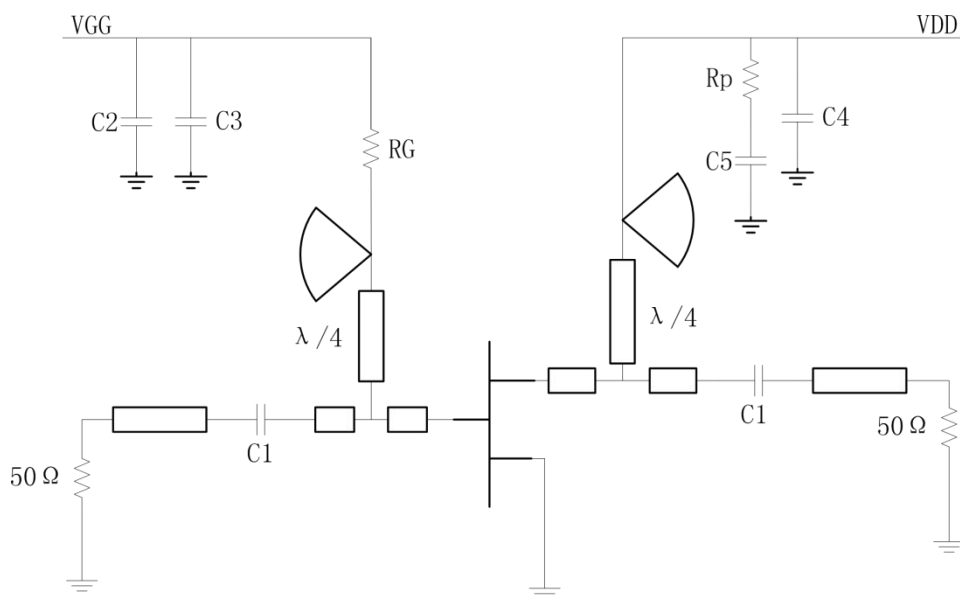
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Recommended circuit :

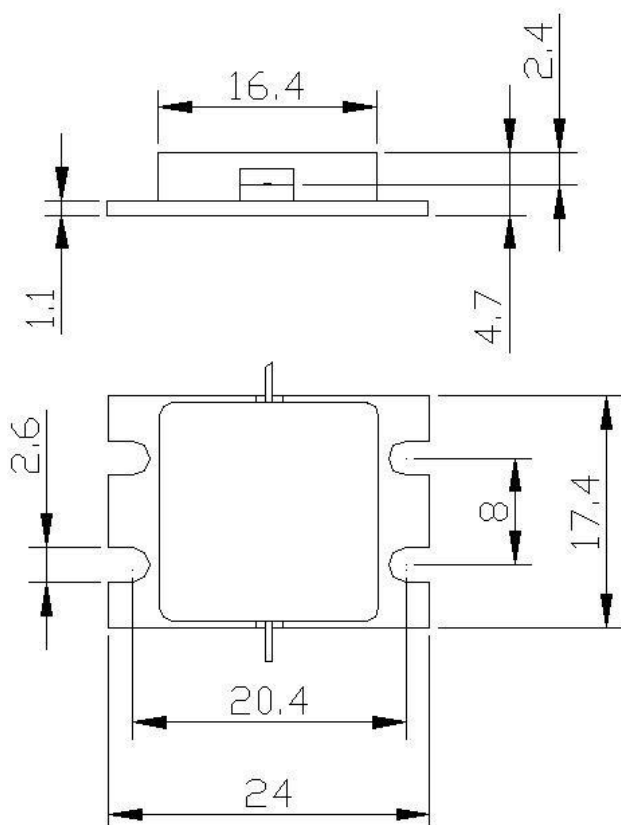


C1:1pF
C2&C5:1nF
C3&C4:10uF
Rp:50Ω
RG:30Ω

Package : IK

ESD	Class III	2000V
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External Dimension :



Precautions for use:

1. Pay attention to drying during transportation and storage.
2. Pay attention to anti-static during the use and assembly of the chip, and wear a grounded anti-static bracelet.
3. Add power to the grid and then add leakage.

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